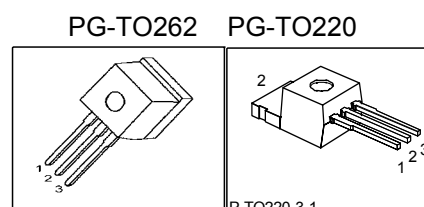


Cool MOS™ Power Transistor

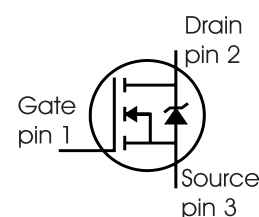
Feature

- New revolutionary high voltage technology
- Worldwide best $R_{DS(on)}$ in TO 220
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved transconductance
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC⁽⁰⁾ for target applications

V_{DS}	600	V
$R_{DS(on)}$	0.6	Ω
I_D	7.3	A



Type	Package	Ordering Code	Marking
SPP07N60S5	PG-TO220	Q67040-S4172	07N60S5
SPI07N60S5	PG-TO262	Q67040-S4328	07N60S5



Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$	I_D	7.3 4.6	A
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\text{ puls}}$	14.6	
Avalanche energy, single pulse $I_D = -A$, $V_{DD} = 50\text{ V}$	E_{AS}	230	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹⁾ $I_D = 7.3\text{ A}$, $V_{DD} = 50\text{ V}$	E_{AR}	0.5	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	7.3	A
Gate source voltage	V_{GS}	± 20	V
Gate source voltage AC ($f > 1\text{ Hz}$)	V_{GS}	± 30	
Power dissipation, $T_C = 25\text{ °C}$	P_{tot}	83	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	°C

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480 \text{ V}$, $I_D = 7.3 \text{ A}$, $T_j = 125 \text{ }^\circ\text{C}$	dv/dt	20	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	1.5	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	K/W
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ²⁾	R_{thJA}	-	-	62	
		-	35	-	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	$^\circ\text{C}$

Electrical Characteristics, at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}$, $I_D=0.25\text{mA}$	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}$, $I_D=7.3\text{A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=350\mu\text{A}$, $V_{GS}=V_{DS}$	3.5	4.5	5.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{V}$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$, $T_j=150^\circ\text{C}$	- -	0.5 -	1 100	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$	-	-	100	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$, $I_D=4.6\text{A}$, $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	- -	0.54 1.46	0.6 -	Ω
Gate input resistance	R_G	$f=1\text{MHz}$, open Drain	-	19	-	

Electrical Characteristics , at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 4.6A$	-	4	-	S
Input capacitance	C_{iss}	$V_{GS} = 0V$, $V_{DS} = 25V$, $f = 1MHz$	-	970	-	pF
Output capacitance	C_{oss}		-	370	-	
Reverse transfer capacitance	C_{rss}		-	10	-	
Effective output capacitance, ³⁾ energy related	$C_{o(er)}$	$V_{GS} = 0V$, $V_{DS} = 0V$ to 480V	-	30	-	pF
Effective output capacitance, ⁴⁾ time related	$C_{o(tr)}$		-	55	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 350V$, $V_{GS} = 0/10V$, $I_D = 7.3A$, $R_G = 12\Omega$	-	120	-	ns
Rise time	t_r		-	40	-	
Turn-off delay time	$t_{d(off)}$		-	170	255	
Fall time	t_f		-	20	30	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 350\text{V}$, $I_D = 7.3\text{A}$	-	7.5	-	nC
Gate to drain charge	Q_{gd}		-	16.5	-	
Gate charge total	Q_g	$V_{DD} = 350\text{V}$, $I_D = 7.3\text{A}$, $V_{GS} = 0\text{ to } 10\text{V}$	-	27	35	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 350\text{V}$, $I_D = 7.3\text{A}$	-	8	-	V

⁰J-STD20 and JESD22

¹Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

²Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

³ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

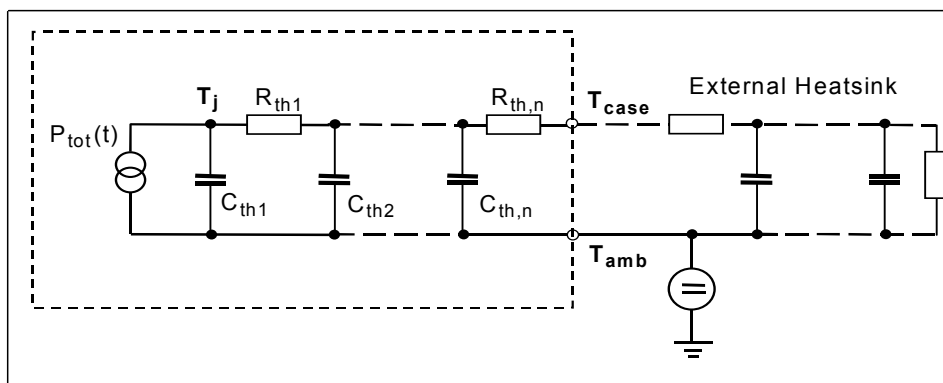
⁴ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	$T_C = 25^\circ\text{C}$	-	-	7.3	A
Inverse diode direct current, pulsed	I_{SM}		-	-	14.6	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}, I_F = I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R = 350\text{V}, I_F = I_S, di_F/dt = 100\text{A}/\mu\text{s}$	-	750	1275	ns
Reverse recovery charge	Q_{rr}		-	4.9	-	

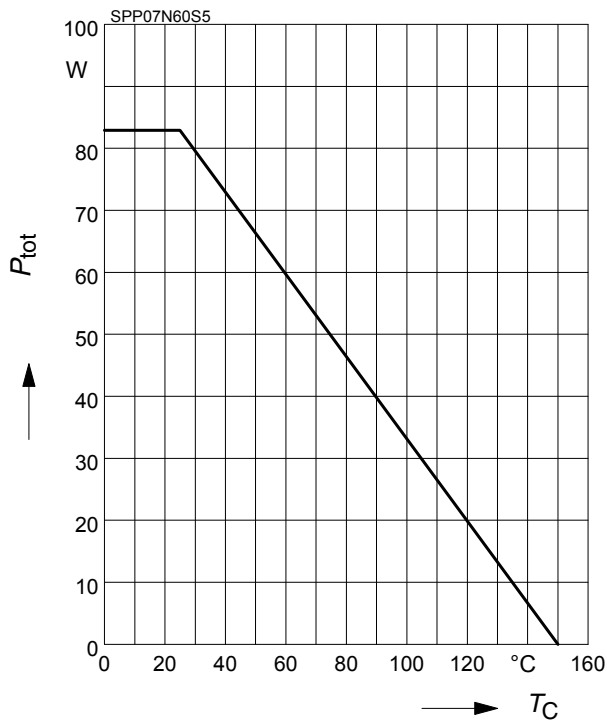
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.024	K/W	C_{th1}	0.00012	Ws/K
R_{th2}	0.046		C_{th2}	0.0004578	
R_{th3}	0.085		C_{th3}	0.000645	
R_{th4}	0.308		C_{th4}	0.001867	
R_{th5}	0.317		C_{th5}	0.004795	
R_{th6}	0.112		C_{th6}	0.045	



1 Power dissipation

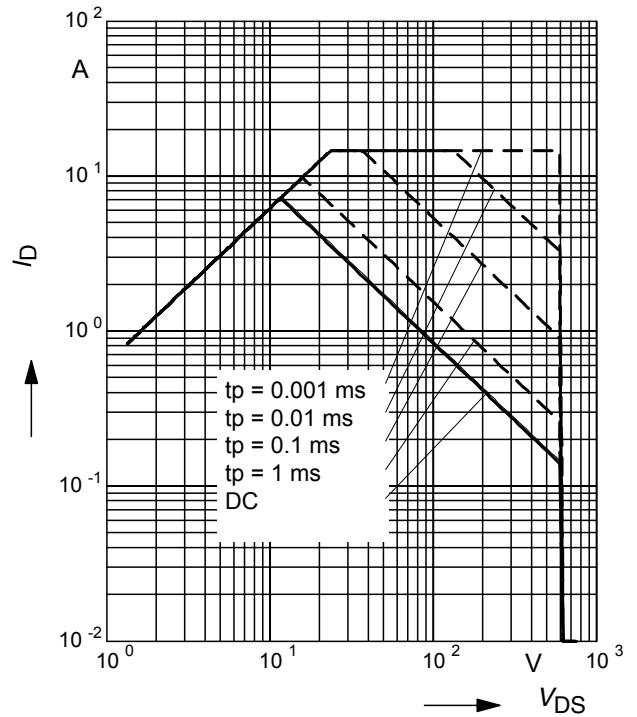
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS})$$

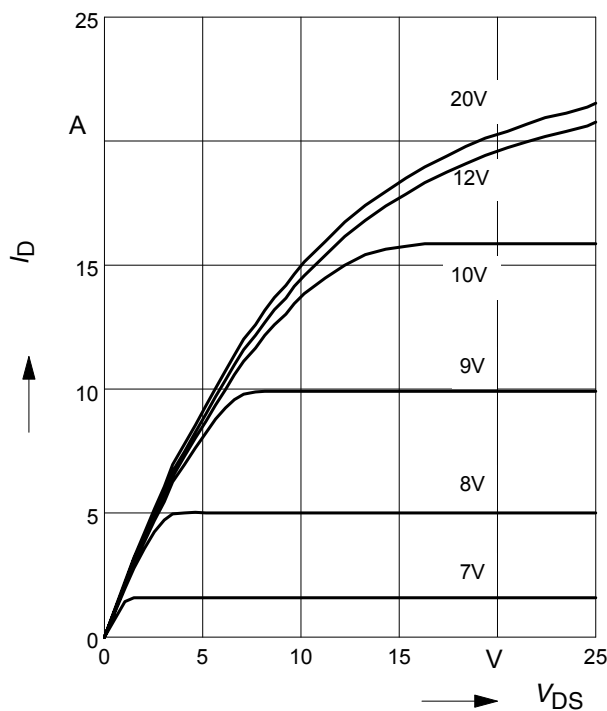
parameter : $D = 0$, $T_C = 25^\circ\text{C}$



3 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

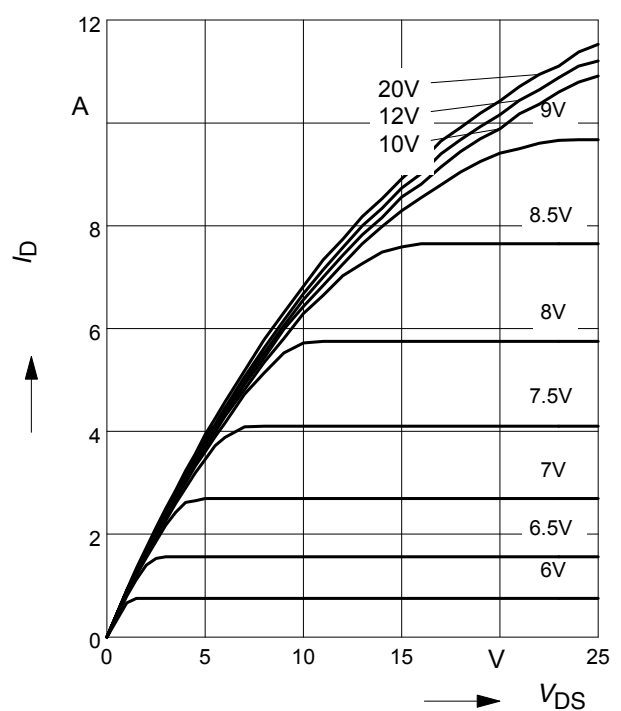
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



4 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

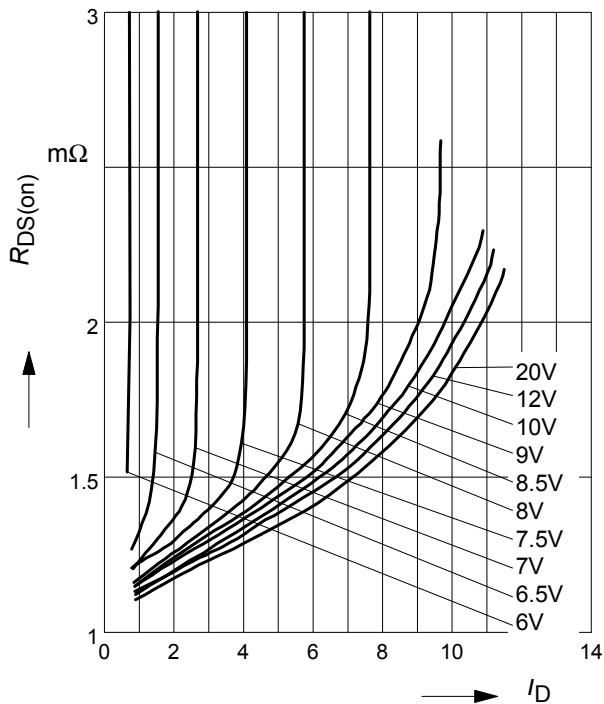
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



5 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

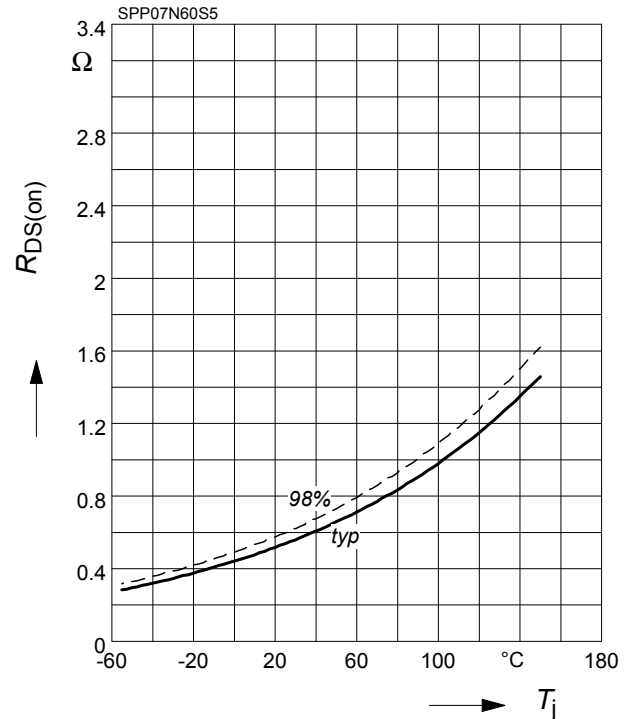
parameter: $T_j = 150^\circ\text{C}$, V_{GS}



6 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

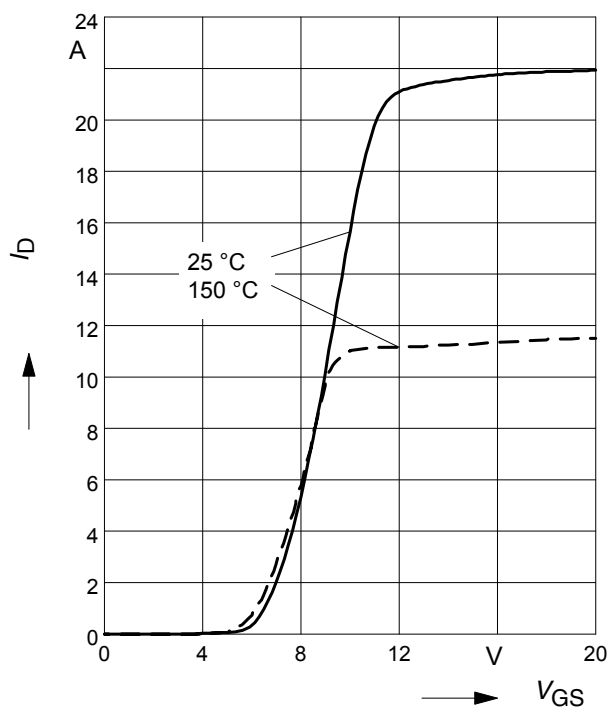
parameter: $I_D = 4.6\text{ A}$, $V_{GS} = 10\text{ V}$



7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

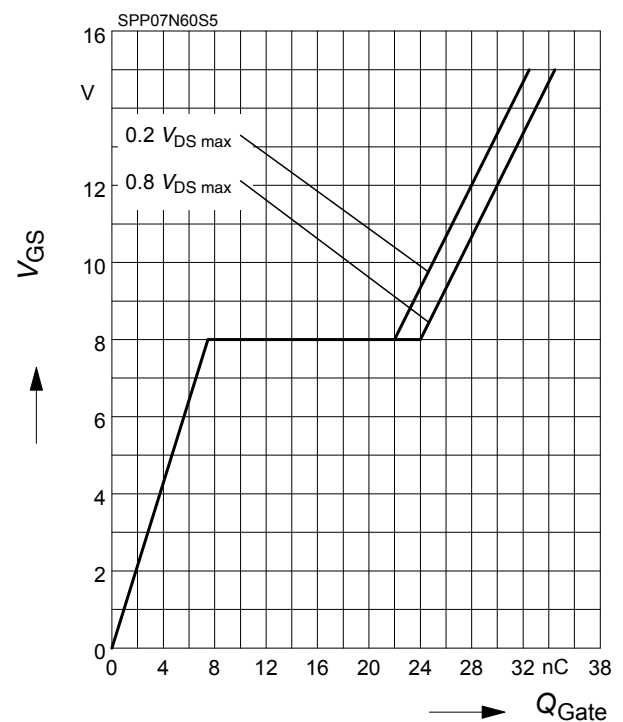
parameter: $t_p = 10\text{ }\mu\text{s}$



8 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

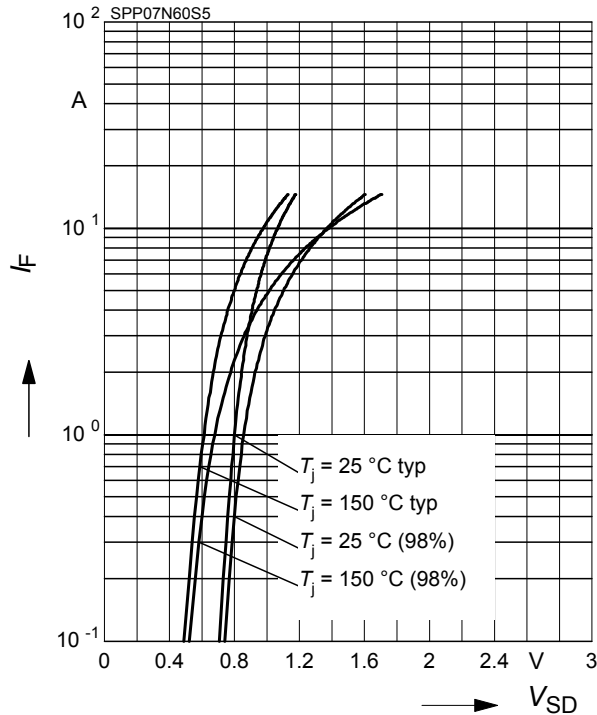
parameter: $I_D = 7.3\text{ A}$ pulsed



9 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

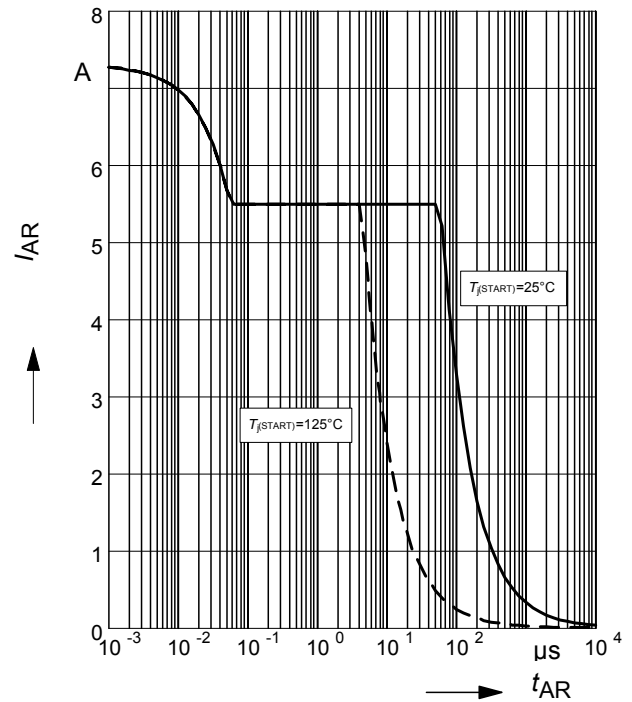
parameter: T_j , $t_p = 10 \mu s$



10 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

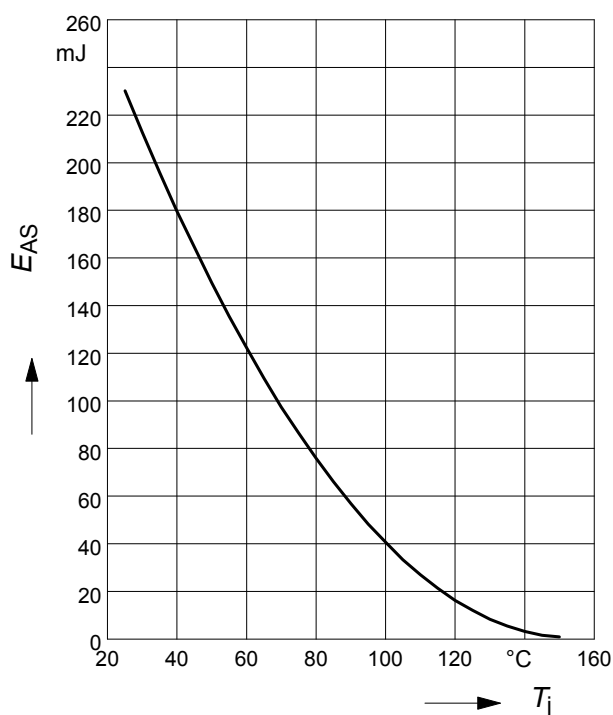
par.: $T_j \leq 150 \text{ } ^\circ\text{C}$



11 Avalanche energy

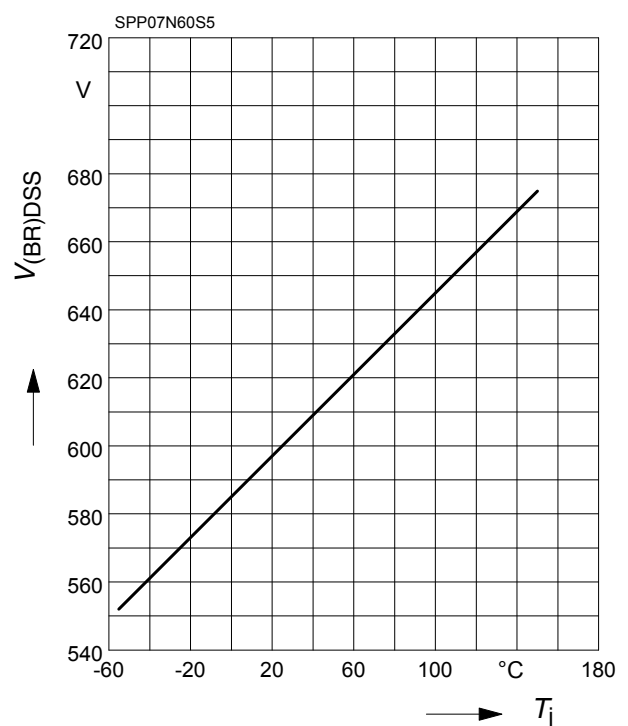
$$E_{AS} = f(T_j)$$

par.: $I_D = -A$, $V_{DD} = 50 V$



12 Drain-source breakdown voltage

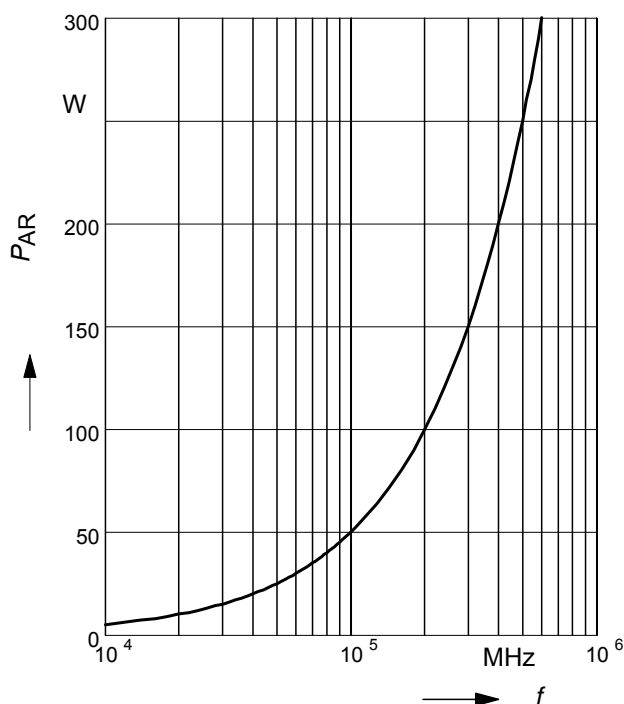
$$V_{(BR)DSS} = f(T_j)$$



13 Avalanche power losses

$$P_{AR} = f(f)$$

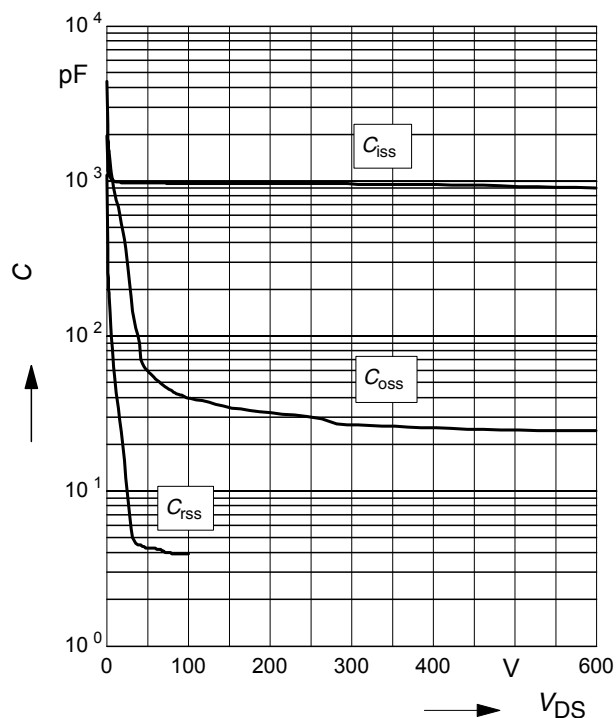
parameter: $E_{AR}=0.5\text{mJ}$



14 Typ. capacitances

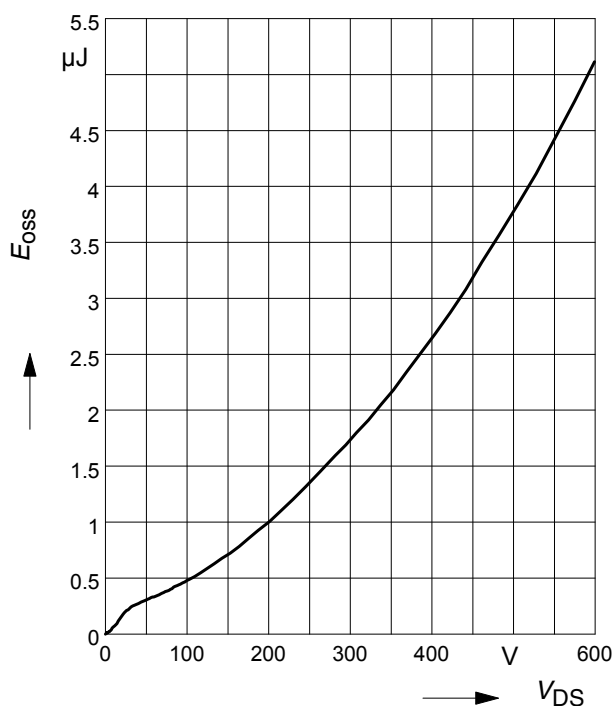
$$C = f(V_{DS})$$

parameter: $V_{GS}=0\text{V}$, $f=1\text{ MHz}$



15 Typ. C_{oss} stored energy

$$E_{oss}=f(V_{DS})$$

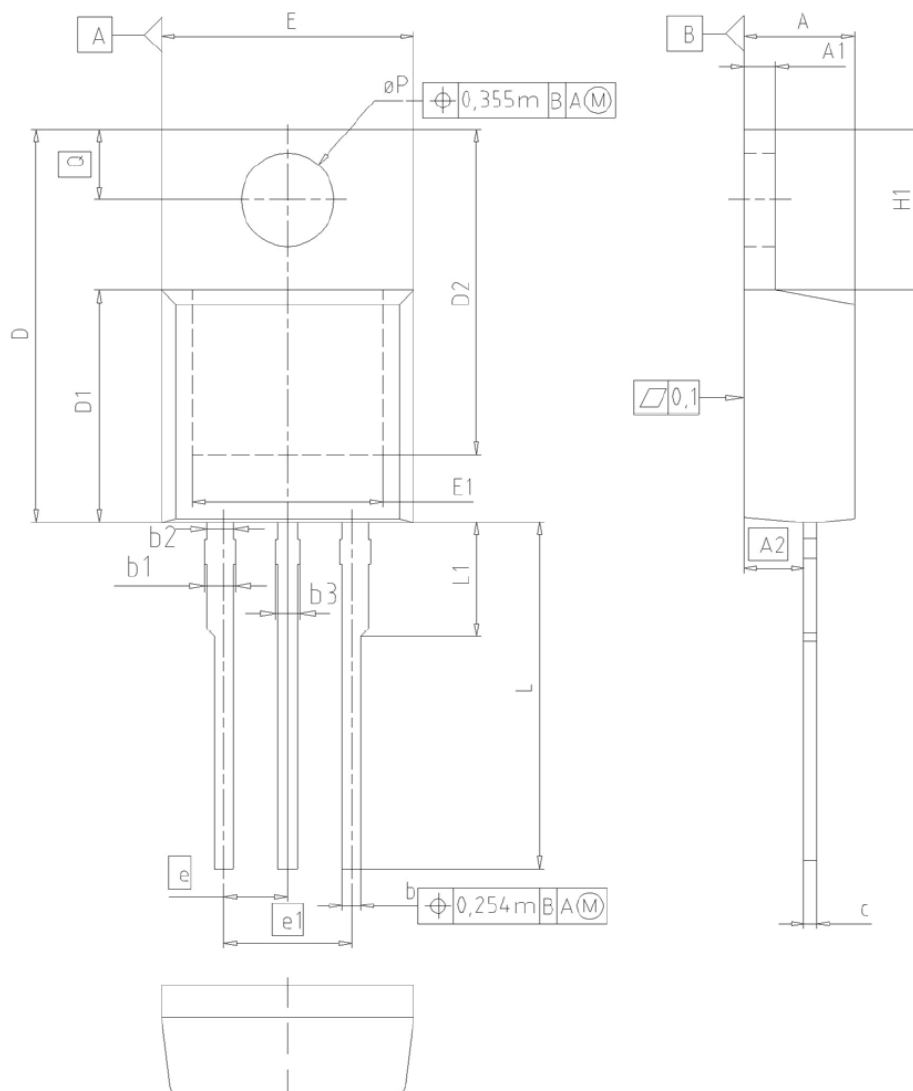


16 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

parameter: $V_{GS} = V_{DS}$

PG-TO220-3-1, PG-TO220-3-21



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

DOCUMENT NO.
Z8B00003318

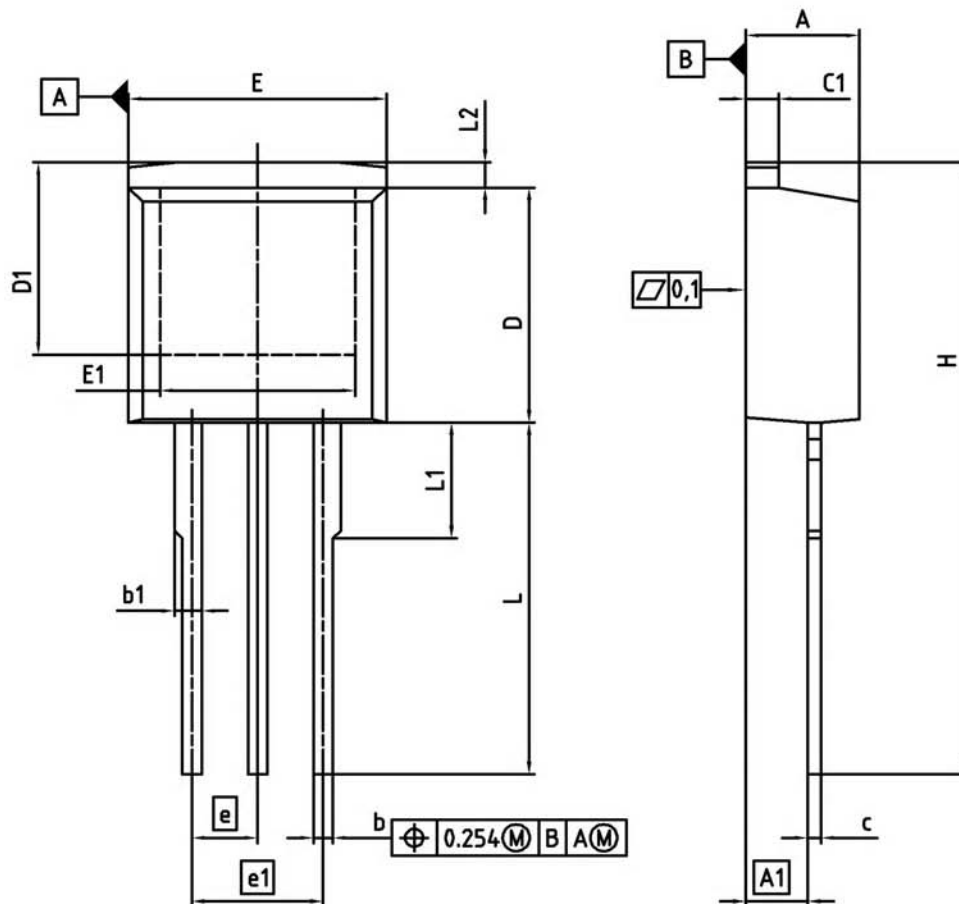
SCALE
0 2.5 5mm

EUROPEAN PROJECTION

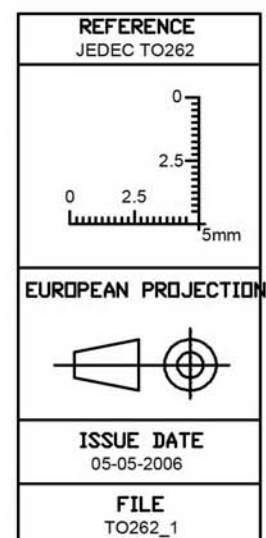
ISSUE DATE
23-08-2007

REVISION
05

PG-TO262-3-1, PG-TO262-3-21 (I²-PAK)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	2.150	2.718	0.085	0.107
b	0.650	0.864	0.026	0.034
b1	0.635	1.400	0.025	0.055
c	0.330	0.600	0.013	0.024
c1	1.170	1.400	0.046	0.055
D	8.509	9.450	0.335	0.372
D1	6.900	-	0.272	-
E	9.700	10.363	0.382	0.408
E1	6.500	8.600	0.256	0.339
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
L	13.000	14.000	0.512	0.551
L1	-	4.800	-	0.189
L2	-	1.727	-	0.068



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